

FOR IMMEDIATE RELEASE
September 30, 2008

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Performance data expanded to include higher frequencies between 5.1 - 5.2GHz and 5.7 - 5.8GHz...

NITRONEX RELEASES 5.1 - 5.8GHZ PERFORMANCE DATA ON ITS 5W GAN-ON-SI RF POWER TRANSISTOR

CHICAGO – WiMAX World, Booth #923, (September 30, 2008) - Nitronex, the global leader in gallium nitride on silicon (GaN-on-Si) RF power transistors for the wireless infrastructure, broadband and military markets, has expanded the performance data of its 28V, 5W class high electron mobility transistor (HEMT) to include frequencies between 5.1 - 5.2GHz and 5.7 - 5.8GHz. Designated the NPTB00004, it achieves 27 dBm (400mW) average output power at 2% EVM in 5.2 GHz WiMAX systems, and 28 dBm (630mW) average output power at 2% EVM in 5.8 GHz WiMAX systems (single carrier OFDM, 64-QAM $\frac{3}{4}$, 8 burst, 20ms frame, 15ms frame data, 3.5MHz channel bandwidth, peak/avg = 10.3dB). This data is now available in the NPTB00004 datasheet available on the Nitronex website.

“This data on the NPTB00004 provides our customers with an ideal solution for WiMAX applications in the 5GHz band of operation,” said Ray Crampton, Director of Marketing at Nitronex. “The NPTB00004 is a uniquely versatile product that, combined with other broadband devices from Nitronex, allows designers to develop power amplifiers for multiple frequency bands using a common power device lineup.”

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NITRONEX RELEASES PERFORMANCE DATA ON ITS 5W GAN ON SI RF POWER TRANSISTOR, P. 2

The NPTB00004 transistors are packaged in a cost-effective plastic over-molded PO150S (similar to a SOIC-8) package with an exposed thermal pad. Samples and application boards are available. Typical pricing is \$9 each in quantities of 1000, with a lead time from stock to ten weeks.

The NPTB00004 transistors are lead-free and RoHS compliant.

For more information about Nitronex's NPTB00004 GaN on Si RF power transistor, contact Nitronex at 2305 Presidential Drive, Durham, NC 27703; call 919-807-9100; e-mail info@nitronex.com; or visit www.nitronex.com.

About Nitronex

Specializing in the development and manufacturing of gallium nitride (GaN) RF power devices, Nitronex is the global leader in high-performance GaN on silicon (GaN on Si) RF power transistors for the commercial wireless infrastructure, broadband and military markets. Based on its patented SIGANTIC[®] process — gallium nitride on silicon technology — Nitronex is at the forefront of commercializing GaN technology for RF applications. The company's ability to combine the disciplines of material growth, wafer processing, device design and wireless applications knowledge is unique to the industry.

Nitronex was founded in 1999 by graduates of the wide bandgap program at North Carolina State University and is headquartered in Durham, North Carolina. It holds 16 patents with 18 others pending.

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